

Dosimetric materials: what do we need to know?

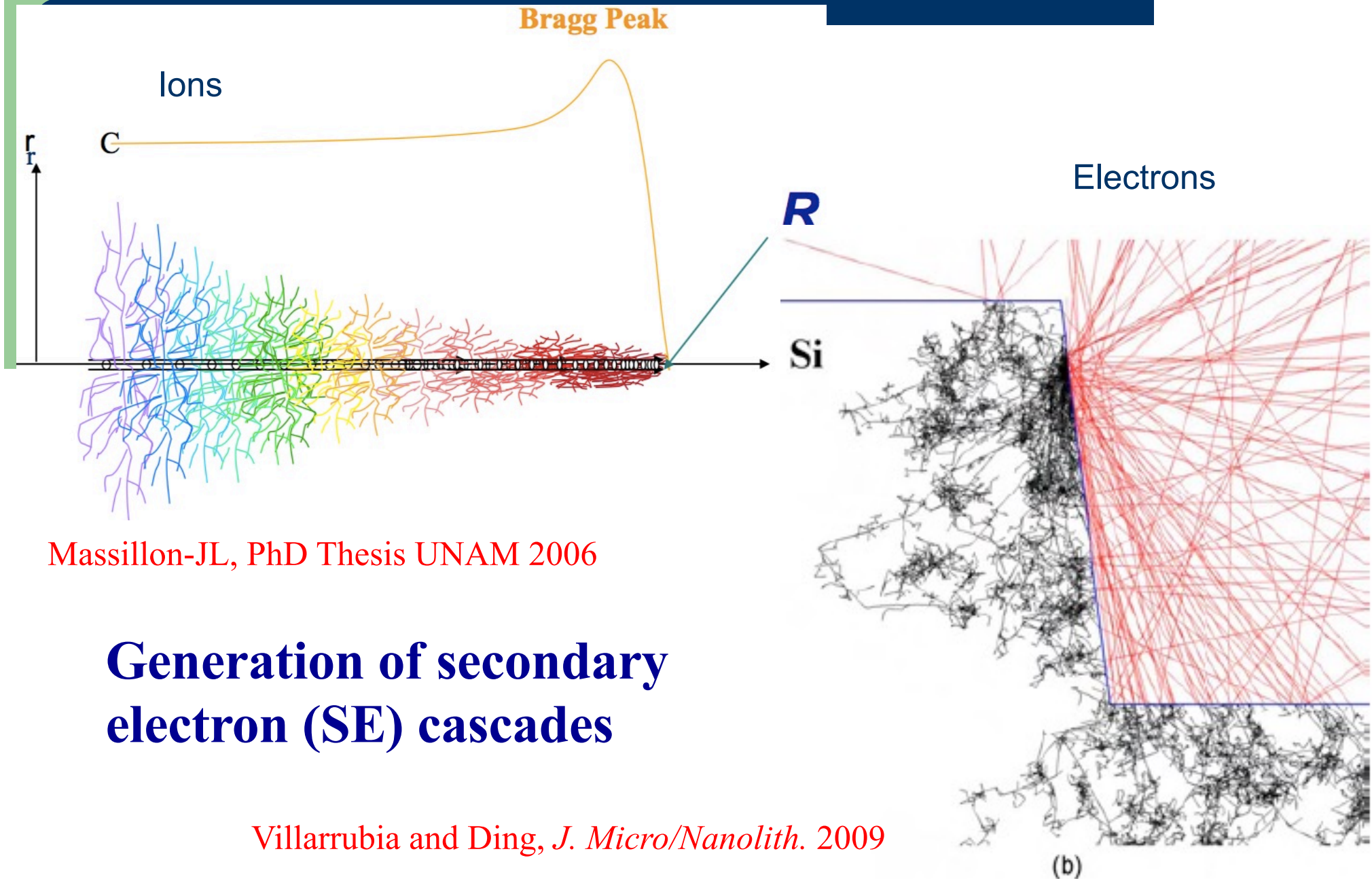


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How can we know the absorbed dose?



Massillon-JL, PhD Thesis UNAM 2006

Generation of secondary electron (SE) cascades

Villarrubia and Ding, *J. Micro/Nanolith.* 2009

Millions of questions ?

Part I

How do these electrons interact with matter?

How many are produced during the interaction?

What is their range?



Irradiated mass?

Part II

Where are the electrons localized?

Is all the energy transformed into a response?

Part I: Cross sections

Electron beam–solid-state interaction model

Interaction between the charge and spin of an incident particle and those of atomic electrons



Relativistic differential cross section (DCS) for inelastic scattering from quantum theory has two components:

1. Longitudinal excitation: The Coulomb interaction exerts a force parallel to the momentum transfer, q .
2. Transverse excitation: Interaction through virtual photons that are perpendicular to q (negligible at $T < 500$ keV)

Part I: Cross-sections

DCS for the longitudinal excitation in terms of the momentum transfer, q

$$\frac{d^2\sigma_L}{d\omega dq} = \frac{2}{\pi N v^2} \mathbf{Im} \left[\frac{-1}{\epsilon(q, \omega)} \right] \frac{1}{q}, \quad \lambda^{-1} = N\sigma$$

$$\frac{d^2\lambda^{-1}}{d\omega dq} = \frac{2}{\pi v^2} \mathbf{Im} \left[\frac{-1}{\epsilon(q, \omega)} \right] \frac{1}{q}$$

N : number density of scatterers

ω and q : energy and momentum transfer

v : incident electron's speed

$\epsilon(q, \omega)$: momentum and energy-dependent dielectric function

$\mathbf{Im}[-1/\epsilon(q, \omega)]$: energy loss function (ELF)

Part I: Cross-sections

The inelastic mean free path (IMFP), λ for an electron can be expressed as

$$\lambda^{-1} = \frac{(1 + T'/c^2)^2}{1 + T'/2c^2} \frac{1}{\pi T'} \int_{\omega_{\min}}^{T' - w_{\text{VB}}} \int_{q^-}^{q^+} \text{Im} \left[\frac{-1}{\epsilon(q, \omega)} \right] \frac{dq}{q} d\omega$$

$$q^{\pm} = \sqrt{T'(2 + T'/c^2)} \pm \sqrt{(T' - \omega)(2 + (T' - \omega)/c^2)}$$

w_{VB} : width of the valence band

ω_{\min} : energy required to promote an electron from the top of the valence band to the bottom of the conduction band

Part I: Stopping power

The stopping power can be calculated from the probability for an electron with relativistic kinetic energy, T , to loss energy per unit distance travelled as:

$$SP = \frac{(1+T'/c^2)^2}{1+T'/2c^2} \frac{1}{\pi T'} \int_{\omega_{\min}}^{T'-w_{\text{VB}}} \int_{q_-}^{q_+} \mathbf{Im} \left[\frac{-1}{\epsilon(q,\omega)} \right] \frac{dq}{q} \omega d\omega,$$

$$q_{\pm} = \sqrt{T'(2 + T'/c^2)} \pm \sqrt{(T' - \omega)(2 + (T' - \omega)/c^2)}$$

$$T' = T - E_g,$$

E_g : the bandgap energy

c : the speed of light,

w_{VB} : the valence band width

$T' - w_{\text{VB}}$: to assure that the incident electron preserves enough energy to stay in the conduction band

ω_{\min} : the minimum energy required to promote an electron from the top of the valence band to the bottom of the conduction band

Part I: Full Penn algorithm (NIST)

$$\mathbf{Im} \left[\frac{-1}{\epsilon(q, \omega)} \right] = - \int_0^\infty d\omega_p G(\omega_p) \mathbf{Im} \left[\frac{-1}{\epsilon_L(q, \omega; \omega_p)} \right],$$

$$G(\omega_p) = - \frac{2}{\pi \omega_p} \mathbf{Im} \left[\frac{-1}{\epsilon(\omega_p)} \right]$$

Due to some limitation on the Lindhard energy loss function, the ELF can be portrayed as a combination of the plasmon pole and the single-electron excitations such as:

$$\mathbf{Im} \left[\frac{-1}{\epsilon(q, \omega)} \right] = \mathbf{Im} \left[\frac{-1}{\epsilon(q, \omega)} \right]_{pl} + \mathbf{Im} \left[\frac{-1}{\epsilon(q, \omega)} \right]_{se}$$

Part I: Full Penn algorithm (NIST)

$$\mathbf{Im} \left[\frac{-1}{\epsilon(q, \omega)} \right]_{pl} = G(\omega_0) \frac{\pi}{[\partial \epsilon_L(q, \omega; \omega_p) / \partial \omega_p]_{\omega_p = \omega_0}} \theta(q^-(\omega; \omega_0) - q),$$

$$q^\pm(\omega; \omega_0) = \pm \left[\omega_p \left(\frac{3\pi}{4} \right)^{1/2} \right]^{1/3} + \left[\omega_p^{2/3} \left(\frac{3\pi}{4} \right)^{1/3} + 2\omega \right]^{1/2}$$

$$\begin{aligned} & \mathbf{Im} \left[\frac{-1}{\epsilon(q, \omega)} \right]_{se} \\ &= \int_0^\infty d\omega_p G(\omega_p) \mathbf{Im} \left[\frac{-1}{\epsilon_L(q, \omega; \omega_p)} \right] \theta(q^+(\omega; \omega_p) - q) \theta(q - q^-(\omega; \omega_p)) \end{aligned}$$

JMONSEL vs Experiment

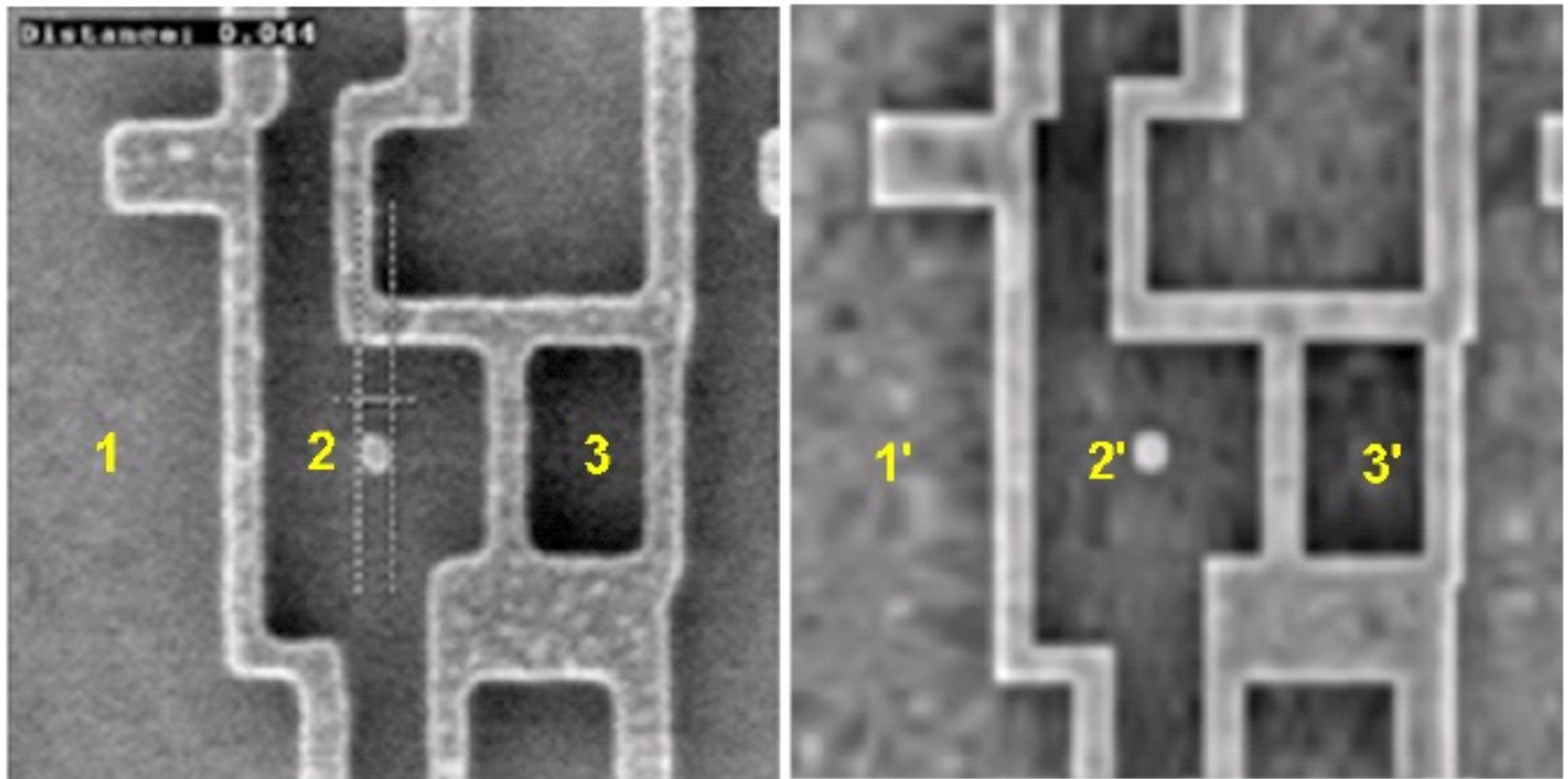


Figure 7. Comparison of measured (left, SEM image, courtesy SEMATECH) and simulated (right) images of an intentional defect array structure. Neighborhoods 1, 2, and 3 (1', 2', and 3' in the simulation) are progressively more confined and also progressively darker. 1 μm fields of view (Figure reproduced from reference 10).

Consistency in the optical data

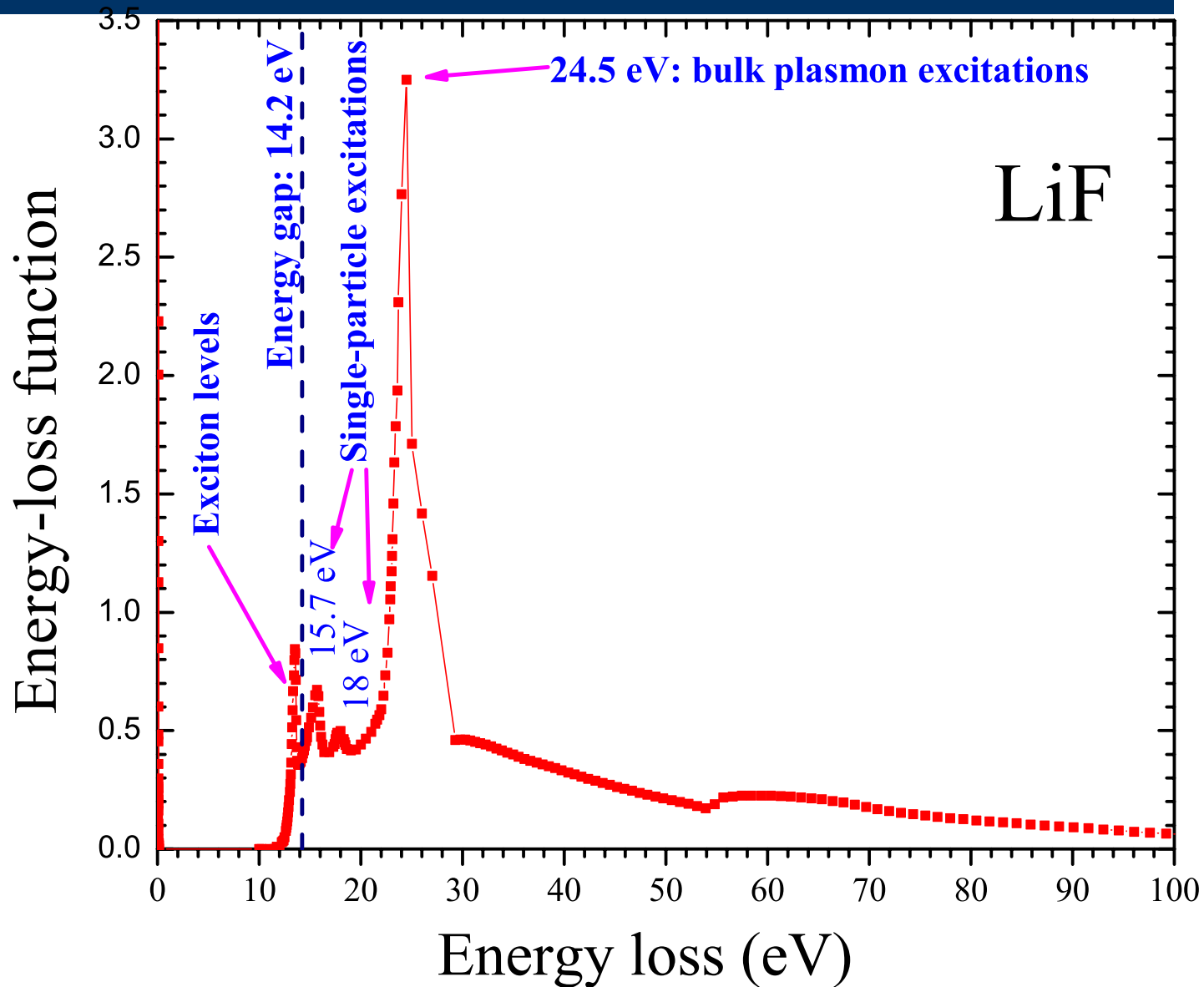
$$P_{\text{eff}} = \frac{2}{\pi} \int_0^{\omega_{\text{max}}} \frac{\text{Im} \left(-\frac{1}{\epsilon(\omega)} \right)}{\omega} d(\omega) + n(0)^{-2}$$

$$Z_{\text{eff}} = -\frac{2m\epsilon_0}{\pi N e^2} \int_0^{\omega_{\text{max}}} \omega \text{Im} \left[\frac{1}{\epsilon(\omega)} \right] d(\omega),$$

Table 1. *KK-sum* and *f-sum* errors.

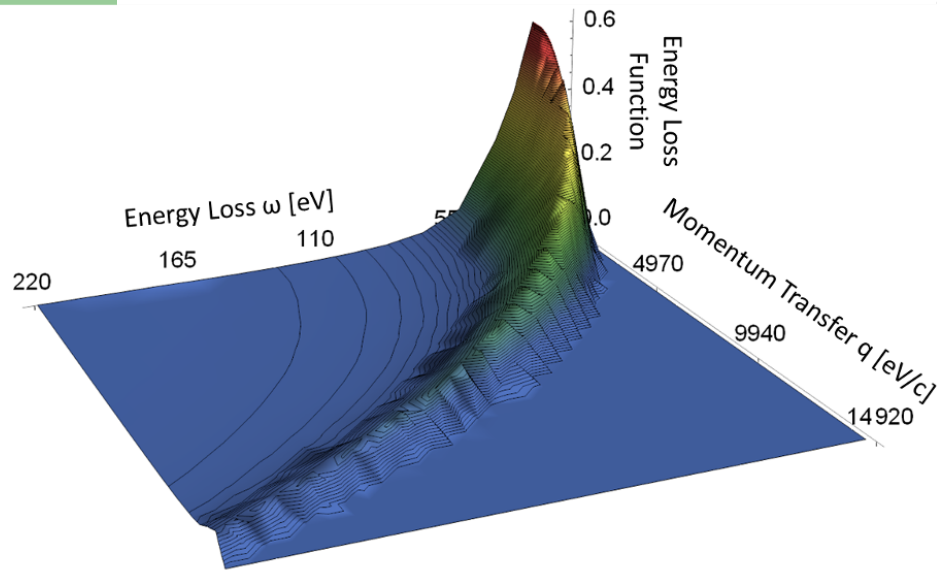
Compound	n(0)	Z	Z _{eff}	f-sum error (%)	P _{eff}	KK-sum error (%)
H ₂ O	8.97	10	10.021	0.21	1.027	2.7
LiF	3	12	13.16	9.69	1.132	13.2
CaF ₂	2.6	38	38.91	2.4	1.058	5.8
Al ₂ O ₃	3.13	50	51.58	3.16	1.038	3.8

Energy-loss function



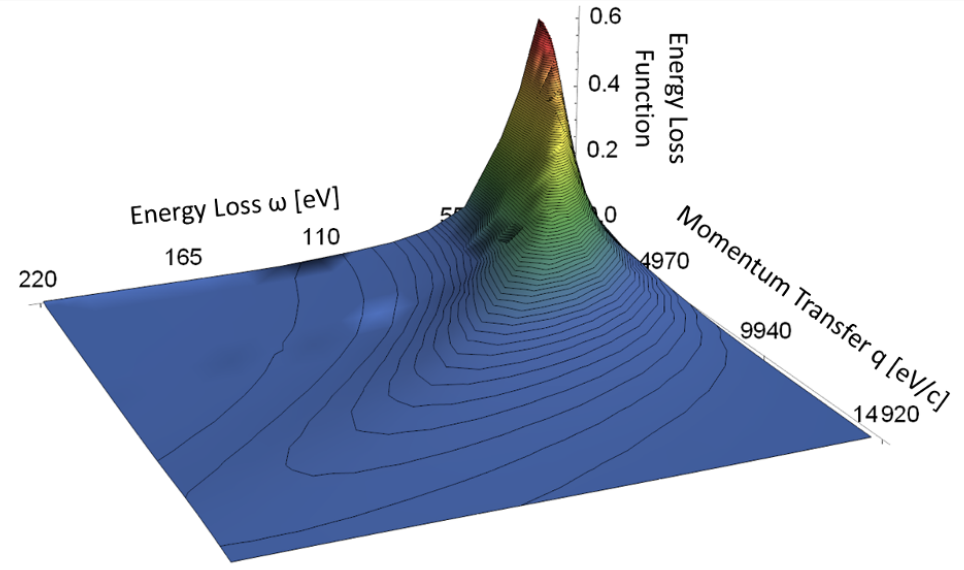
ELF vs momentum vs energy loss

SPA



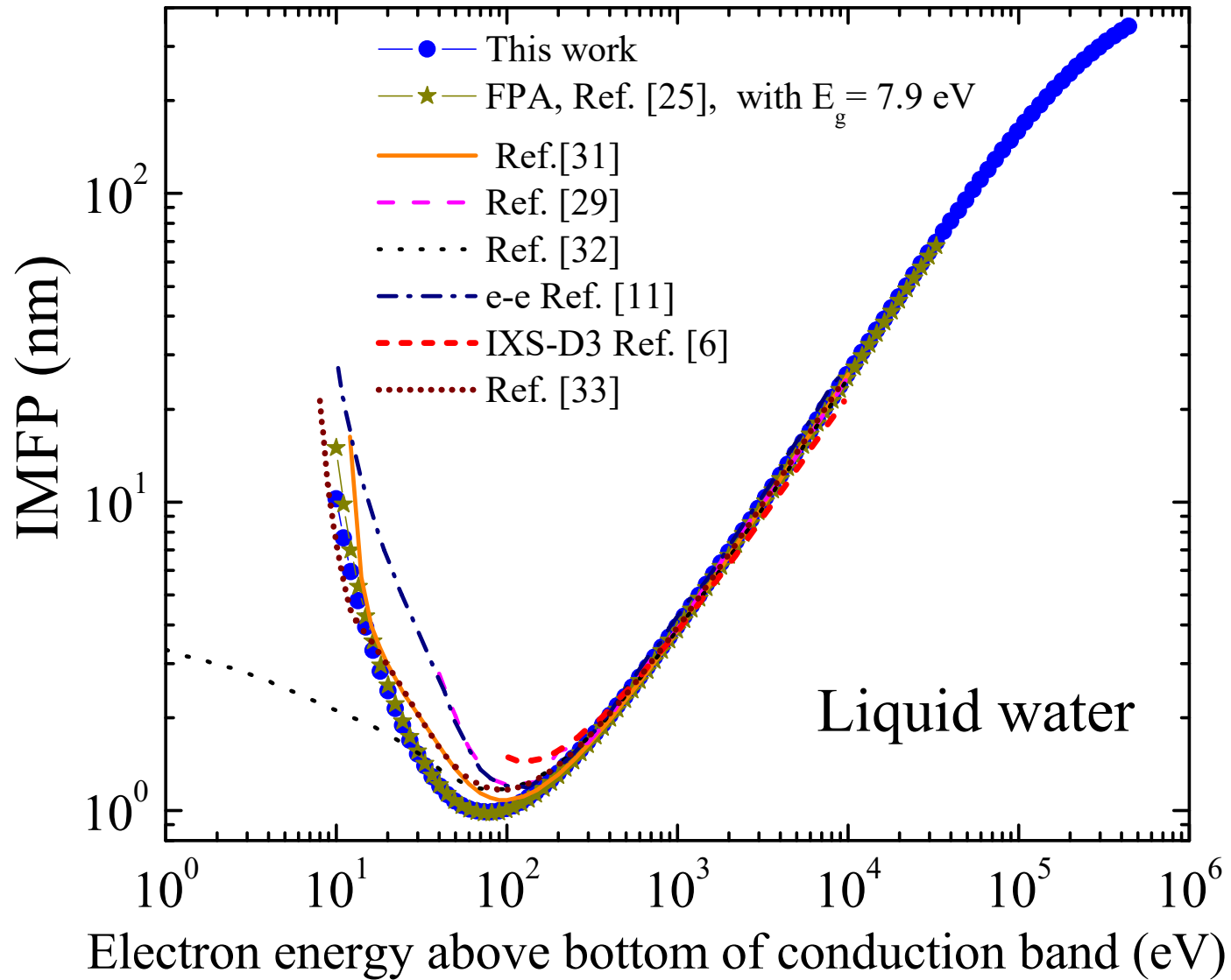
FPA

$q \neq 0$

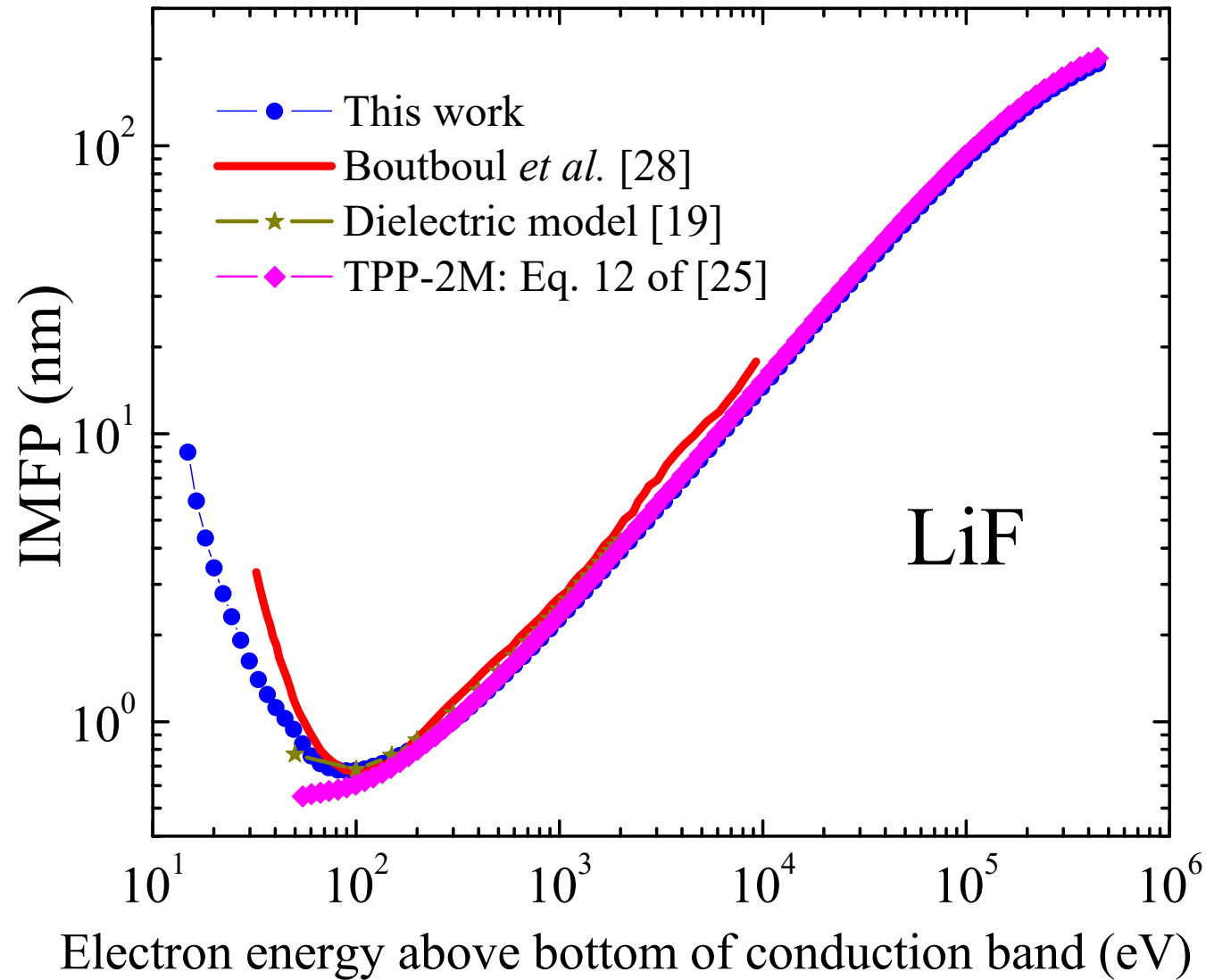


Perspective view of ELF as a function of momentum transfer and energy loss calculated by the FPA for liquid water

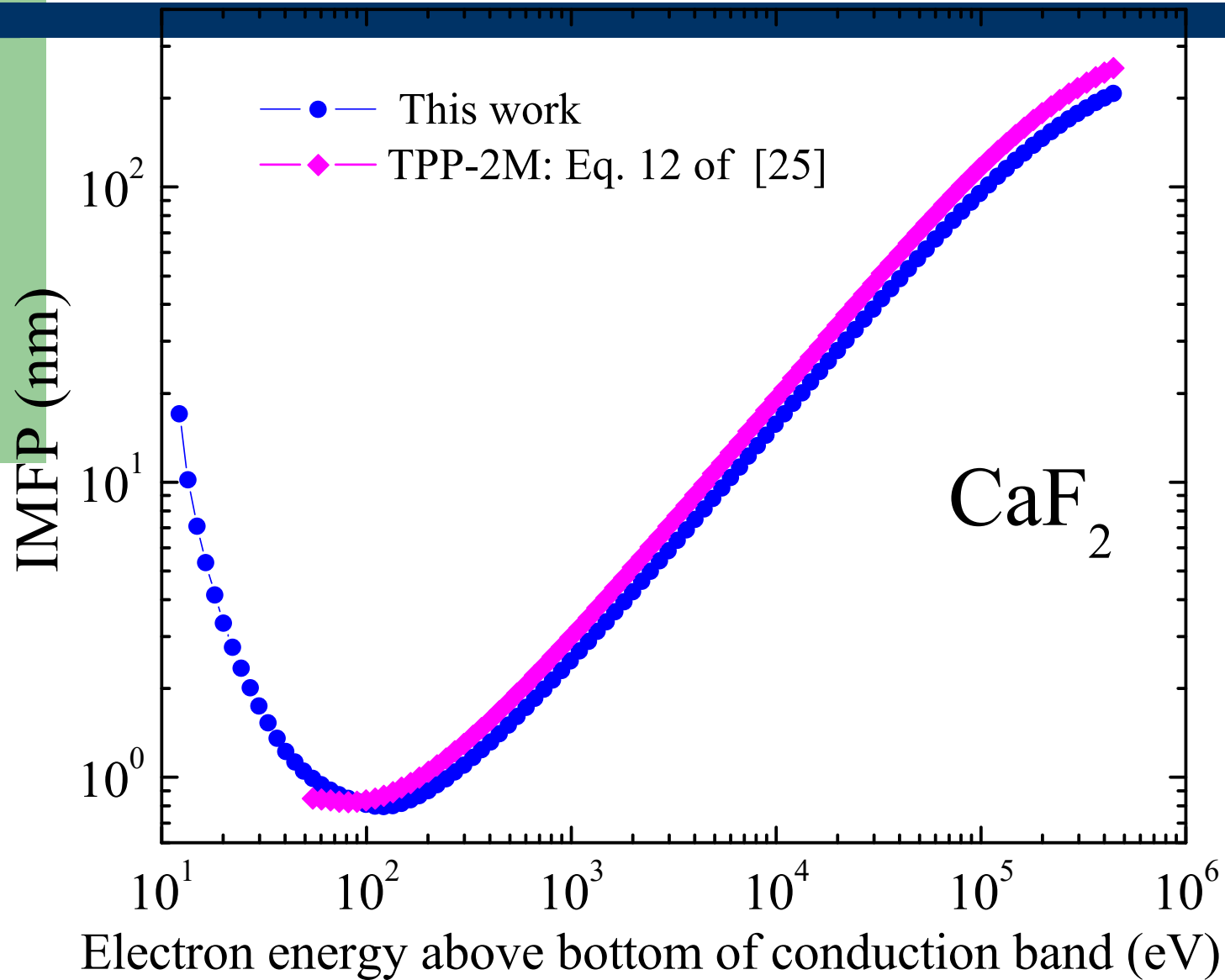
Electron mean free path



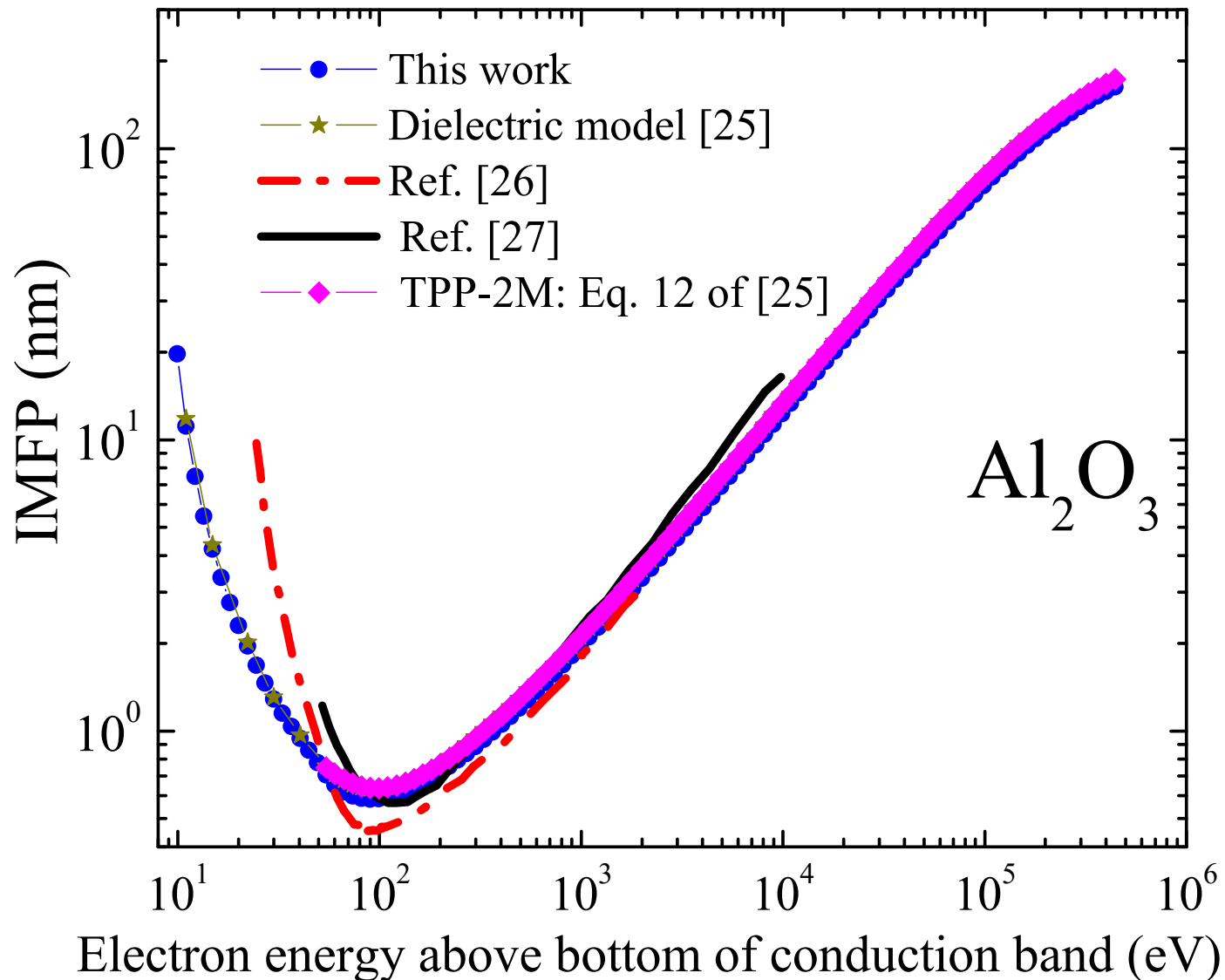
Electron mean free path



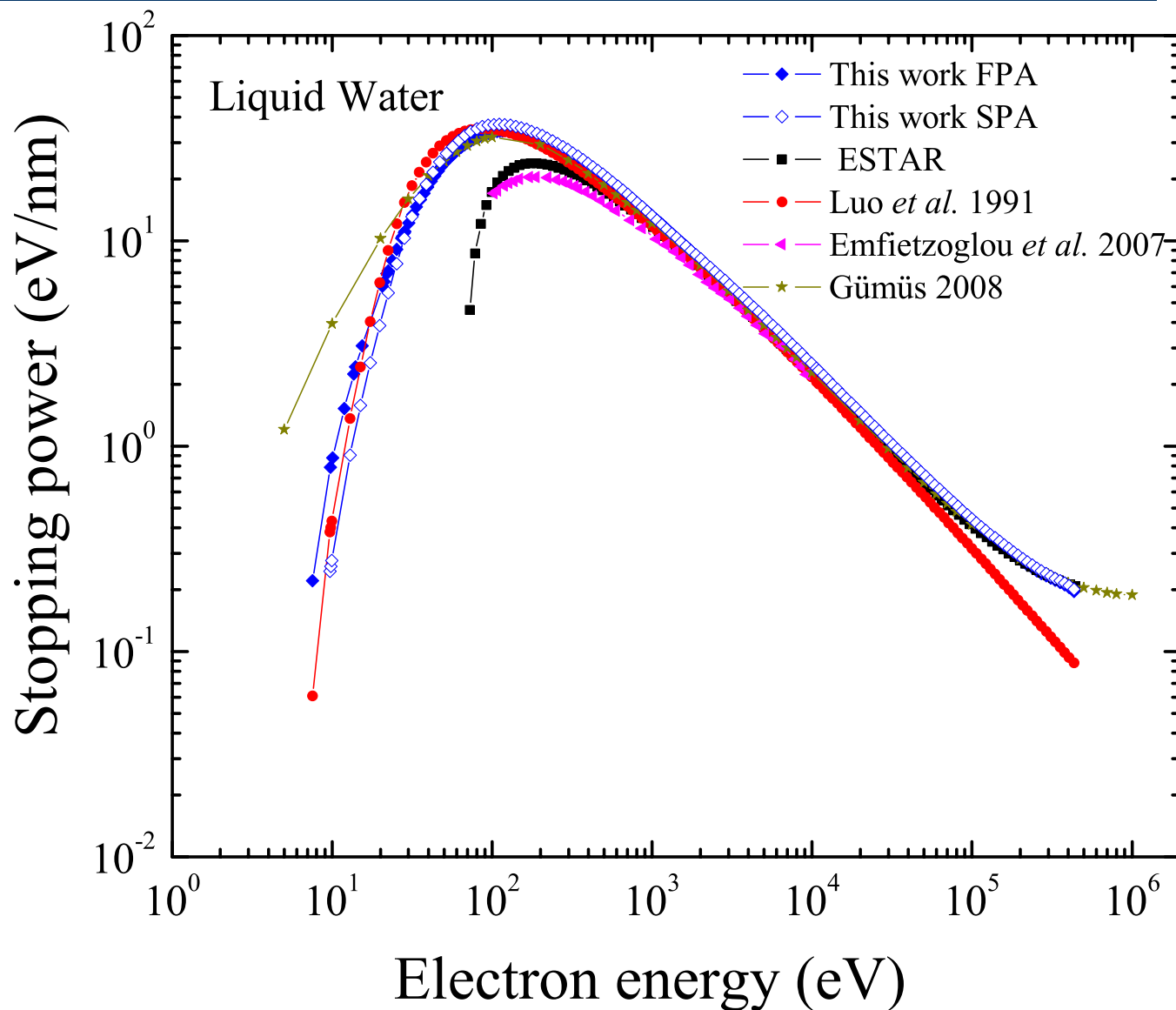
Electron mean free path



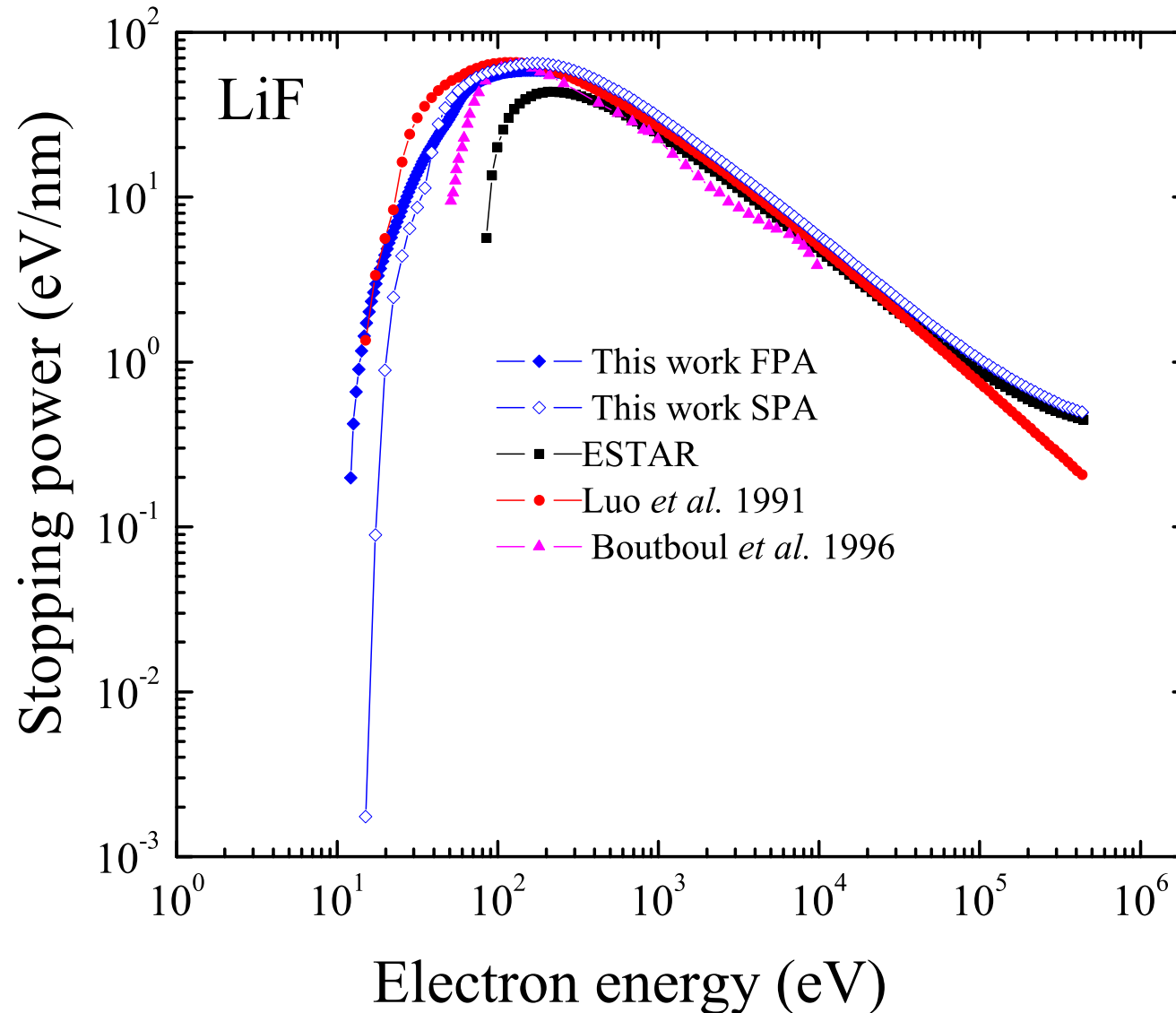
Electron mean free path



Electron Stopping power using linear response: The dielectric model



Electron Stopping power using linear response: The dielectric model



Part II: LiF:Mg,Ti?

During the last few years, density functional theory (DFT) has been considered as a suitable tool to study radiation effects and electronic structures of:

Ti, Mg-doped LiF



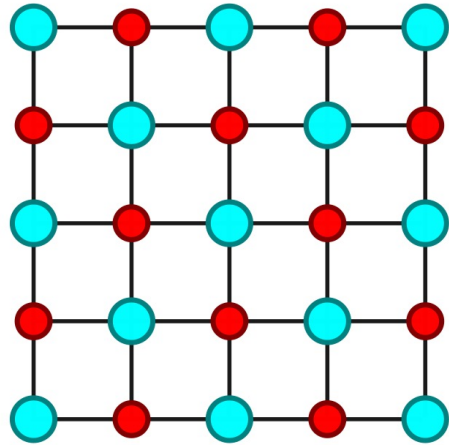
Massillon-JL et al. *J. Phys.:Condens. Matter* **31**
(2019) 025502

Massillon-JL et al. *Radiat. Meas.* **174** (2024) 107114

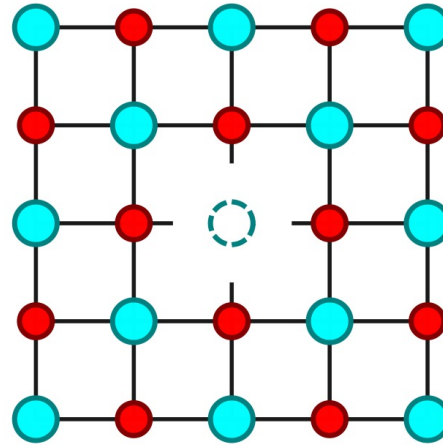


Modak and Modak,
*Computational Materials
Science* **202** (2022) 110977

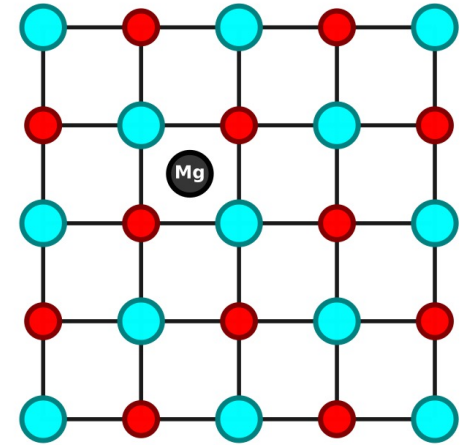
Simplified illustrative structures for the initial configurations



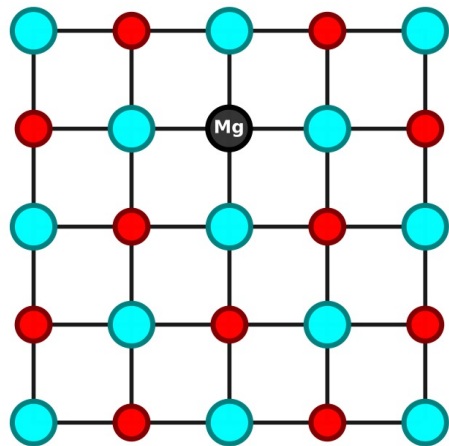
(a) LiF



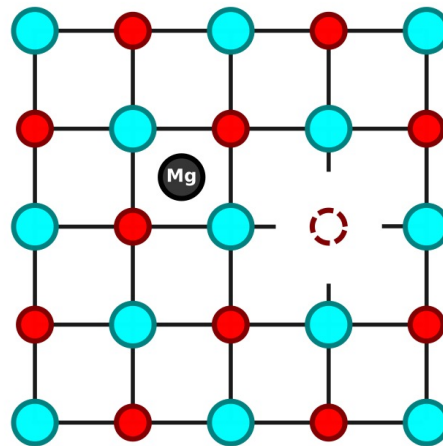
(b) LiF-F_{vac}



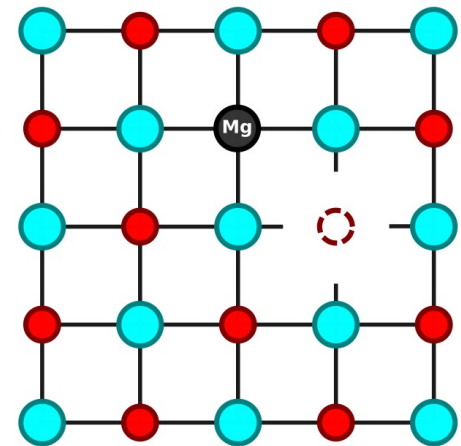
(c) LiFMg



(d) LiFMg-Li_{sub}

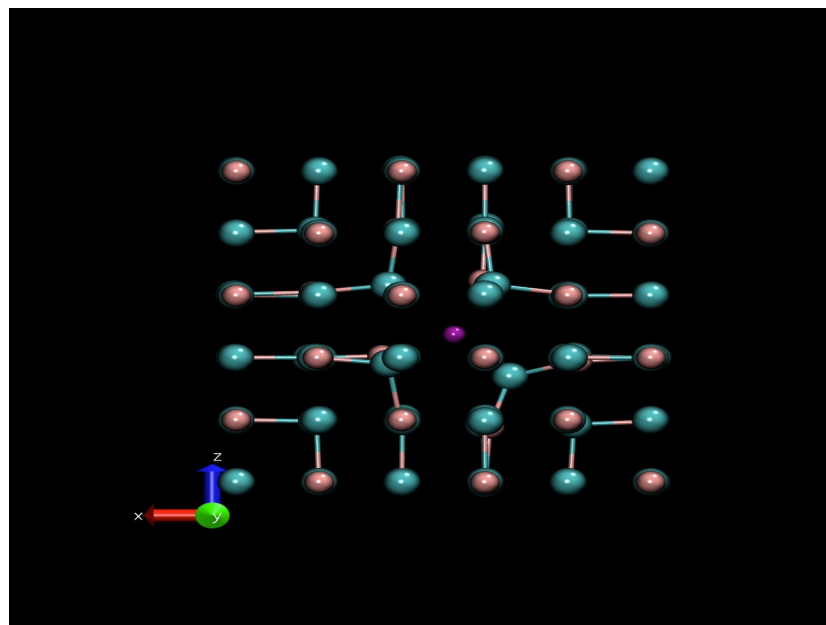


(e) LiFMg-Li_{vac}



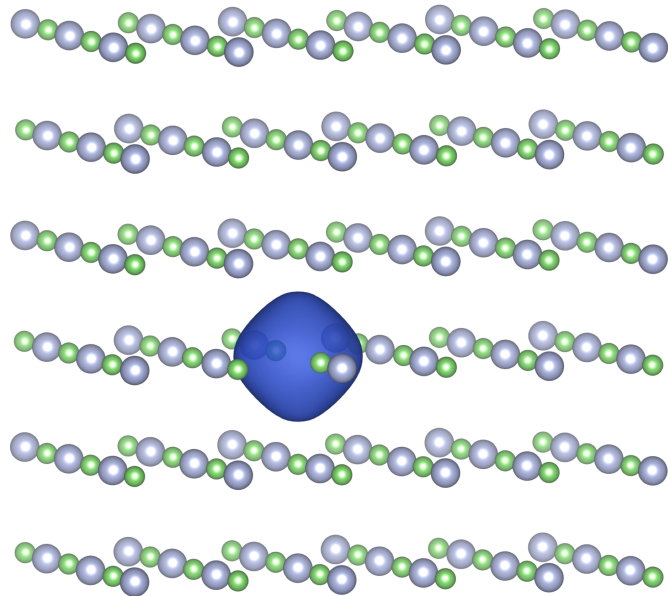
(f) LiFMg-Li_{sub}-Li_{vac}

Molecular dynamic simulation of LiF:Mg

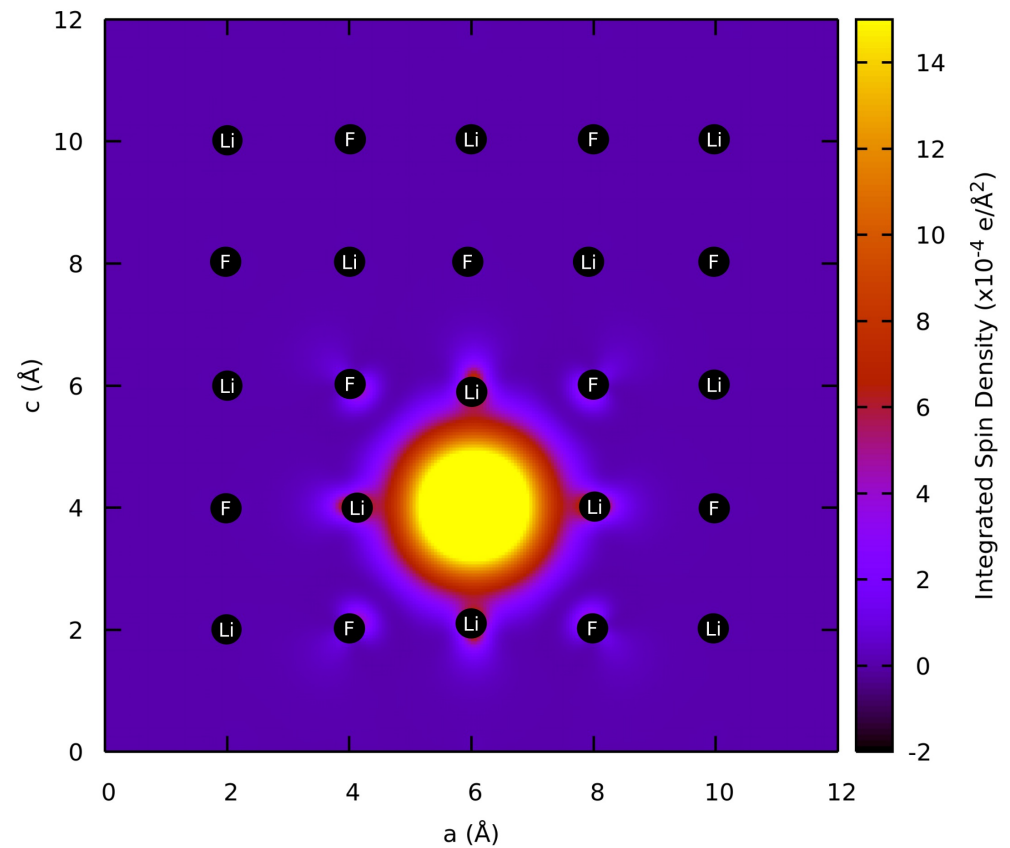


Fluorine vacancy in LiF

Spin density isosurface of the LiF:F vacancy

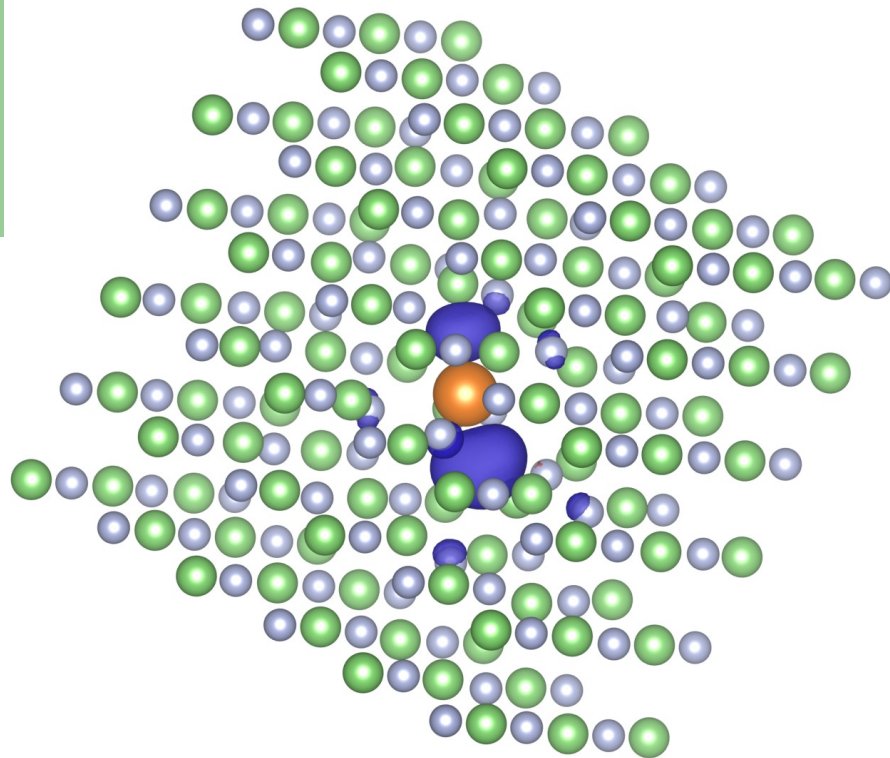


Two-dimensional contour plot of the F vacancy spin density

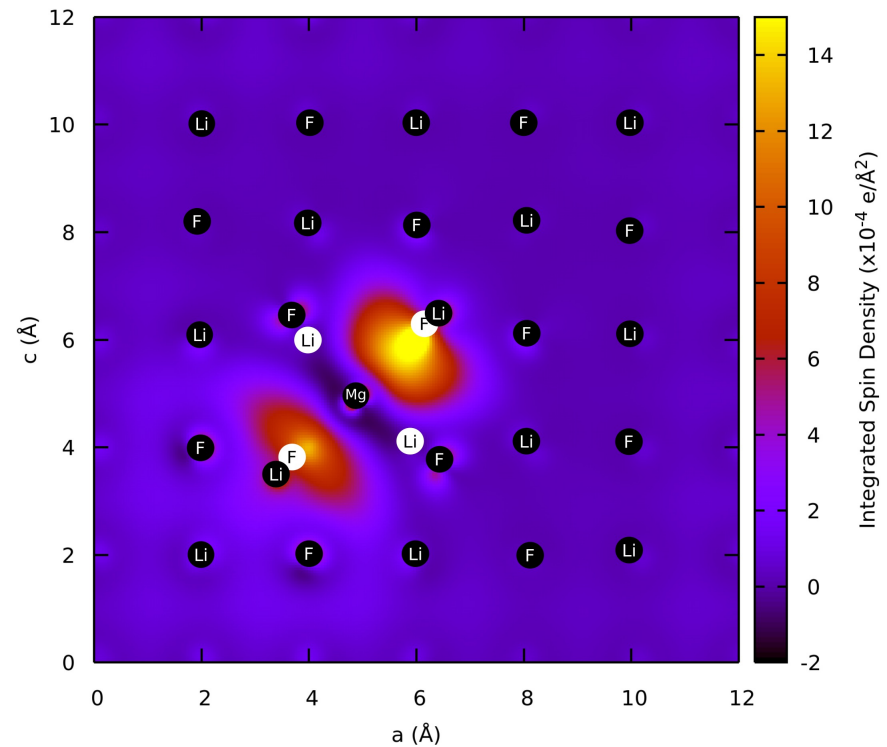


Mg dopant in LiF

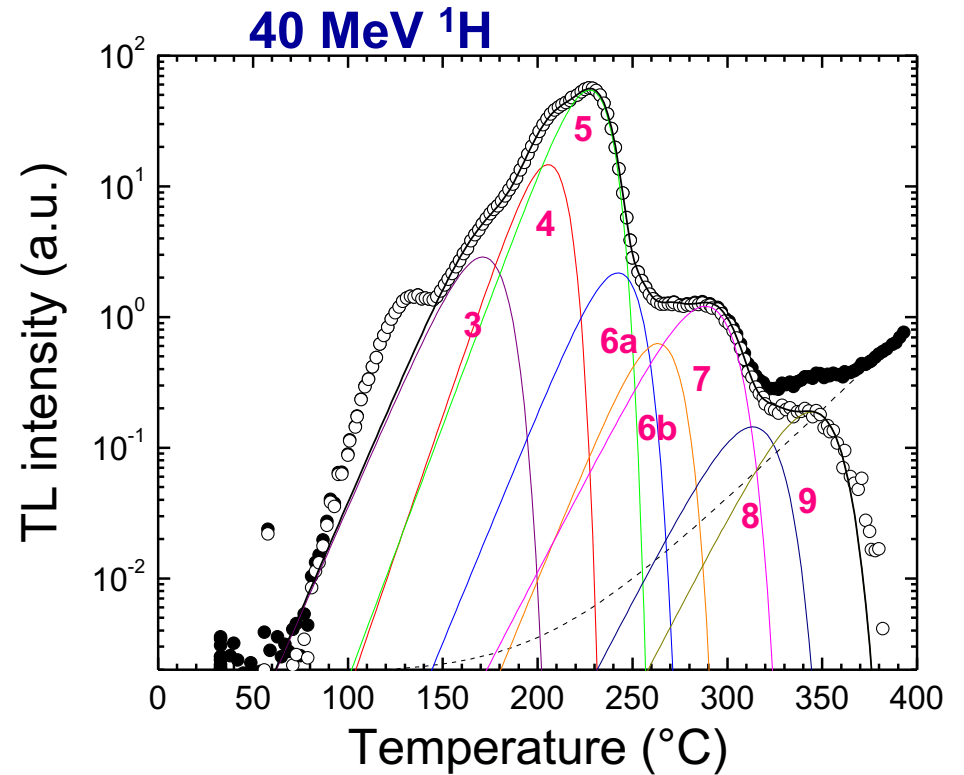
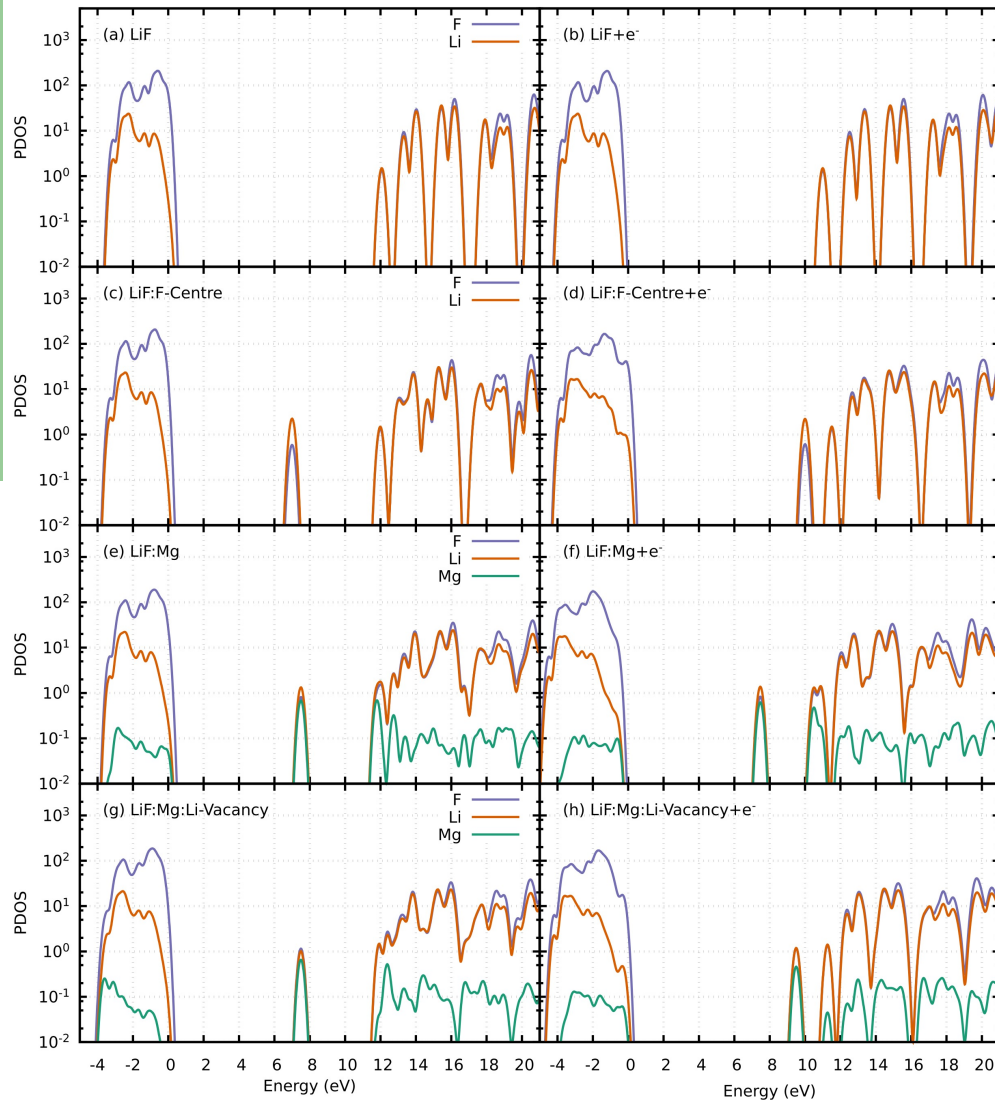
Spin density isosurface of the LiF:Mg with excess electron



Two-dimensional contour plot of the LiF:Mg+e⁻ spin density



Density of states for LiF:Mg



G Massillon-JL, PhD Thesis UNAM 2006

Energy level of the defects in LiF:Mg

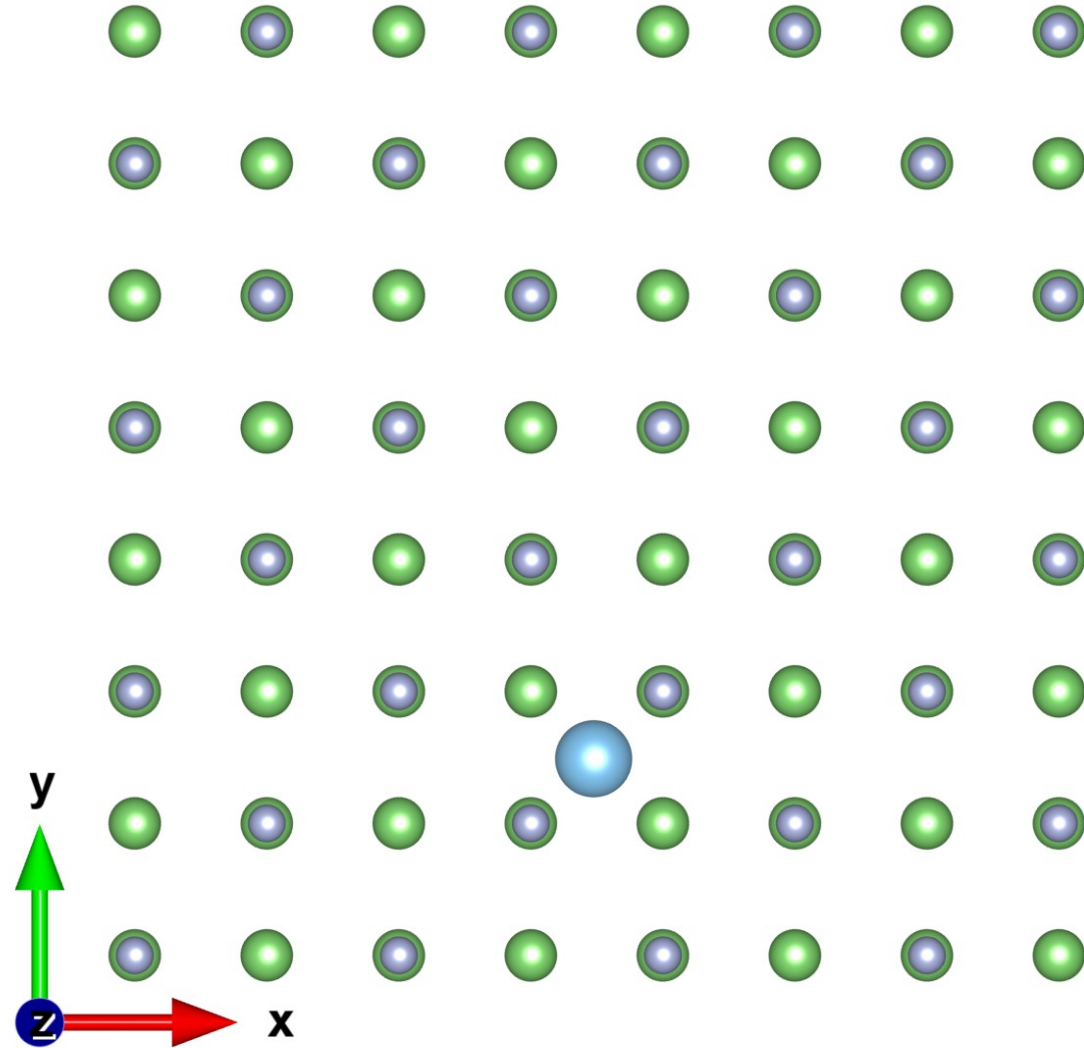
Table 1. Kohn–Sham energy levels of the defects, $E_{\text{CBM}} - E_{\text{DS}}$, in eV.

Defect-state	PBE	PBE0	<u>Experiment</u>
LiF-gap	9.06	12.075	<u>14.2 + 2 [44]</u>
F vacancy 1	3.420	<u>5.064</u>	<u>5.061 [11]</u>
F vacancy 2	1.629	<u>1.866</u>	—
LiF:Mg	2.270	<u>4.534</u>	<u>4.428 [10–15]</u>
(LiF:Mg + e^-) ¹	2.268	<u>4.865</u>	—
(LiF:Mg + e^-) ²	—	<u>4.224</u>	<u>4.000 [10–15]</u>
(LiF:Mg + e^-) ³	—	2.688	—
(LiF:Mg–Li _{vac}) ¹	2.557	4.487	—
(LiF:Mg–Li _{vac}) ²	1.461	1.584	—
LiF:Mg–Li _{vac} + e^-	2.514	<u>4.544</u>	—
(LiF:Mg–Li _{sub}) ¹	1.092	2.889	—
(LiF:Mg–Li _{sub}) ²	0.728	0.919	—
LiF:Mg–Li _{sub} + e^-	1.785	<u>3.486</u>	<u>3.263 [10–15]</u>
LiF:Mg–Li _{sub} –Li _{vac}	—	—	—
(LiF:Mg–Li _{sub} –Li _{vac} + e^-) ¹	1.095	<u>2.898</u>	—
(LiF:Mg–Li _{sub} –Li _{vac} + e^-) ²	<u>0.730</u>	<u>0.922</u>	—

Illustrative structure for the initial configuration of LiF:Ti

Atom symbols

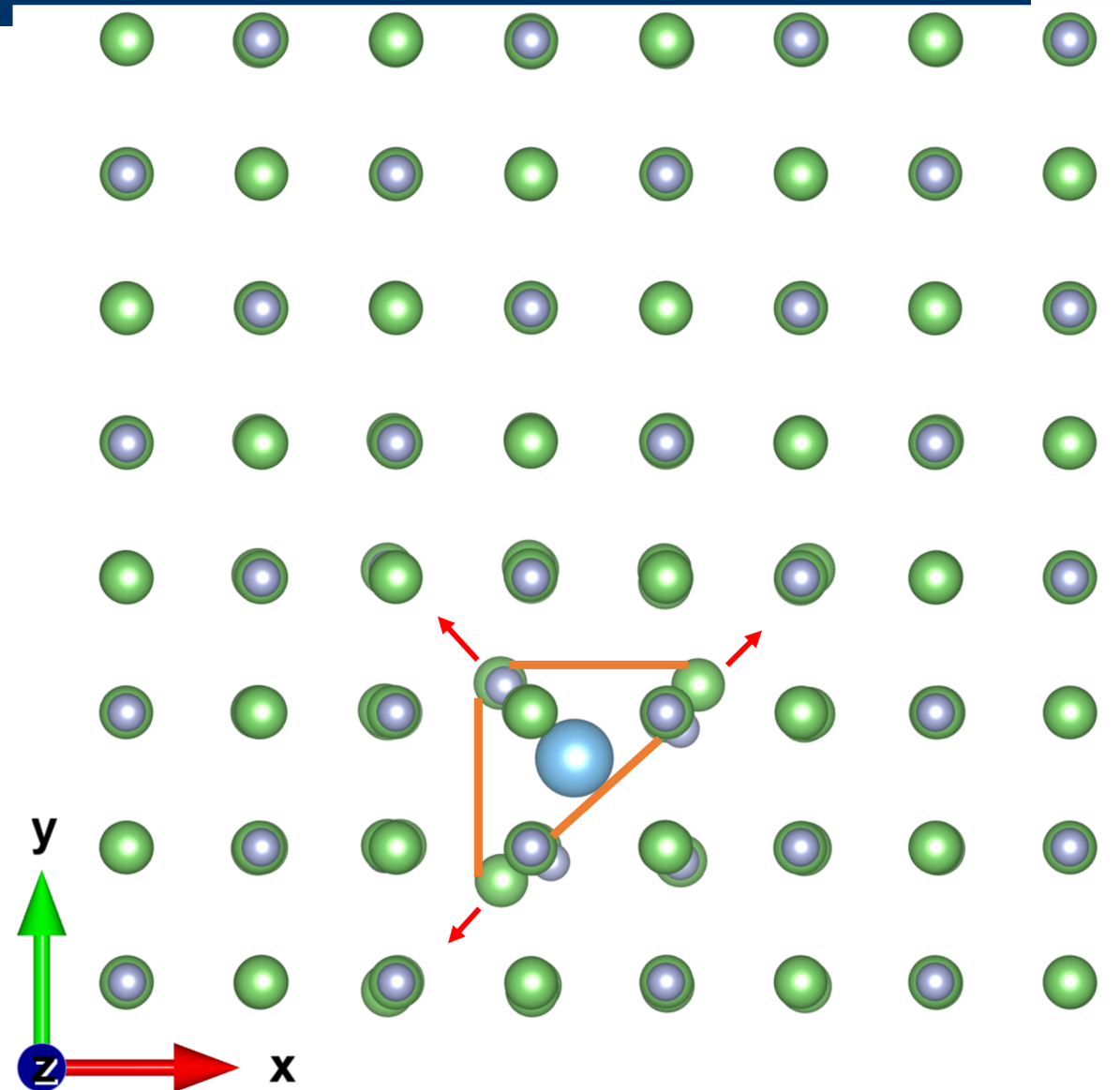
- ❖ Grey: F
- ❖ Green: Li
- ❖ Cyan: Ti



Geometry configuration of LiF:Ti after relaxation

Atom symbols

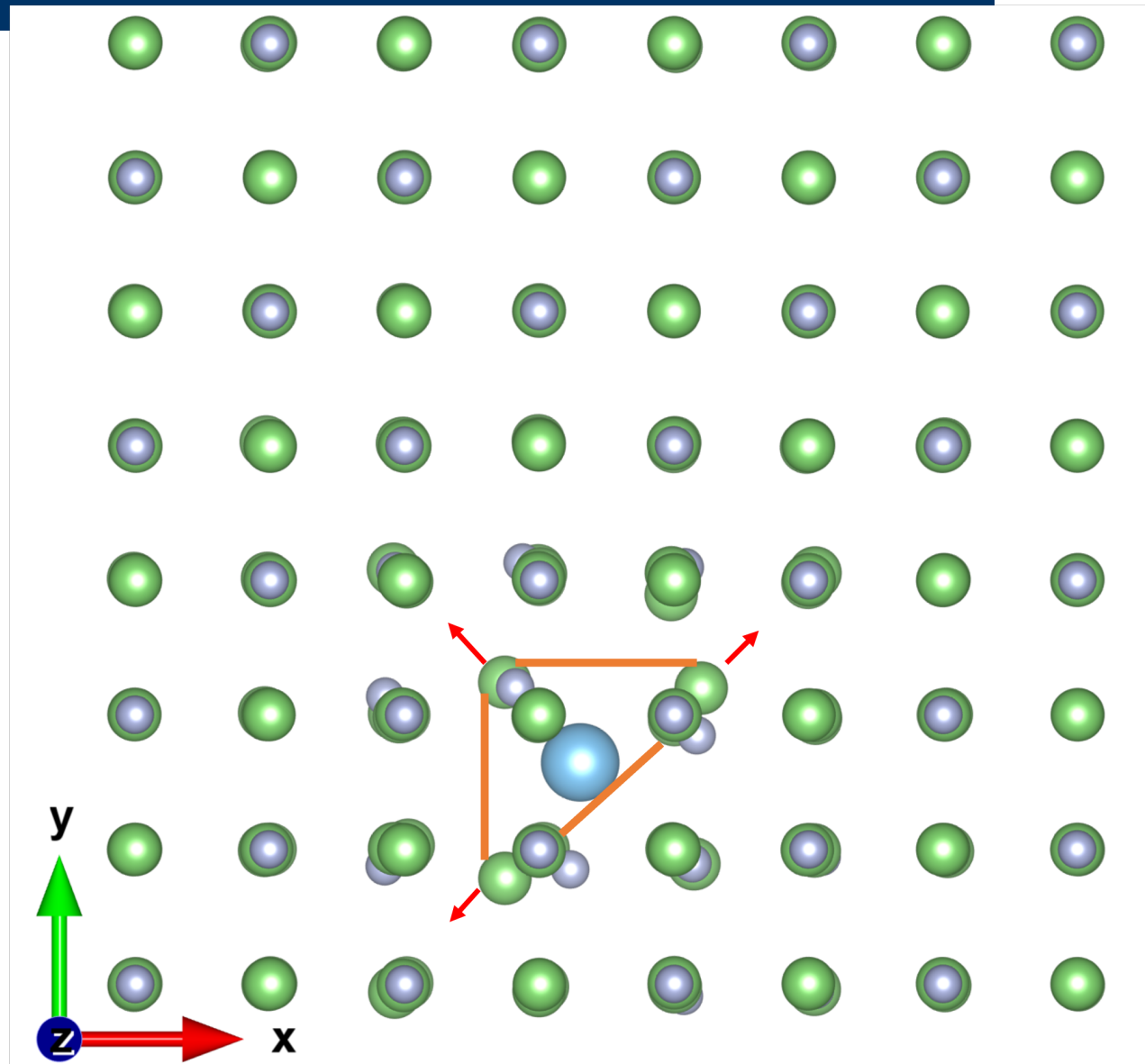
- ❖ Grey: F
- ❖ Green: Li
- ❖ Cyan: Ti



LiF:Ti with an excess electron after relaxation

Atom symbols

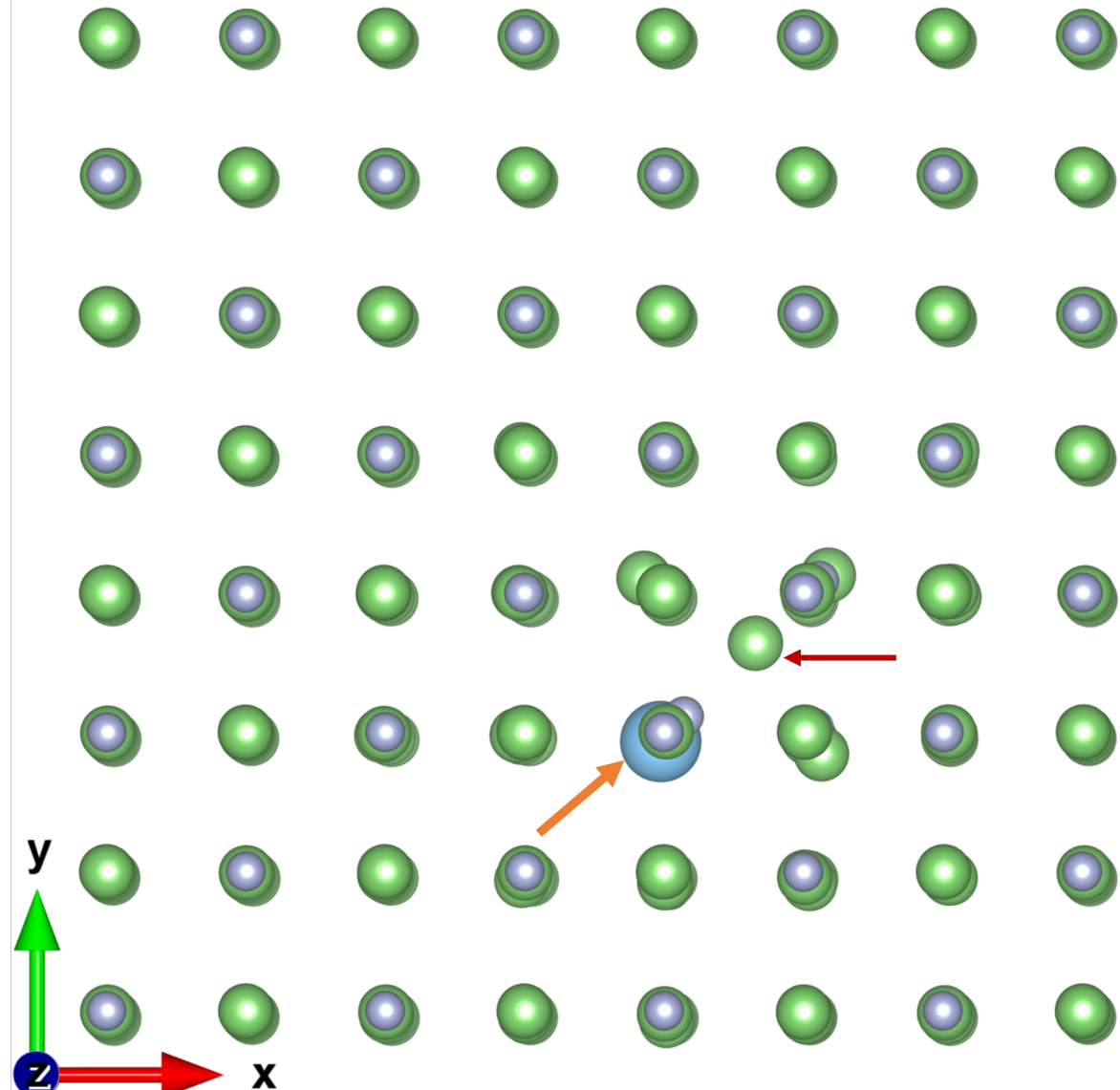
- ❖ Grey: F
- ❖ Green: Li
- ❖ Cyan: Ti



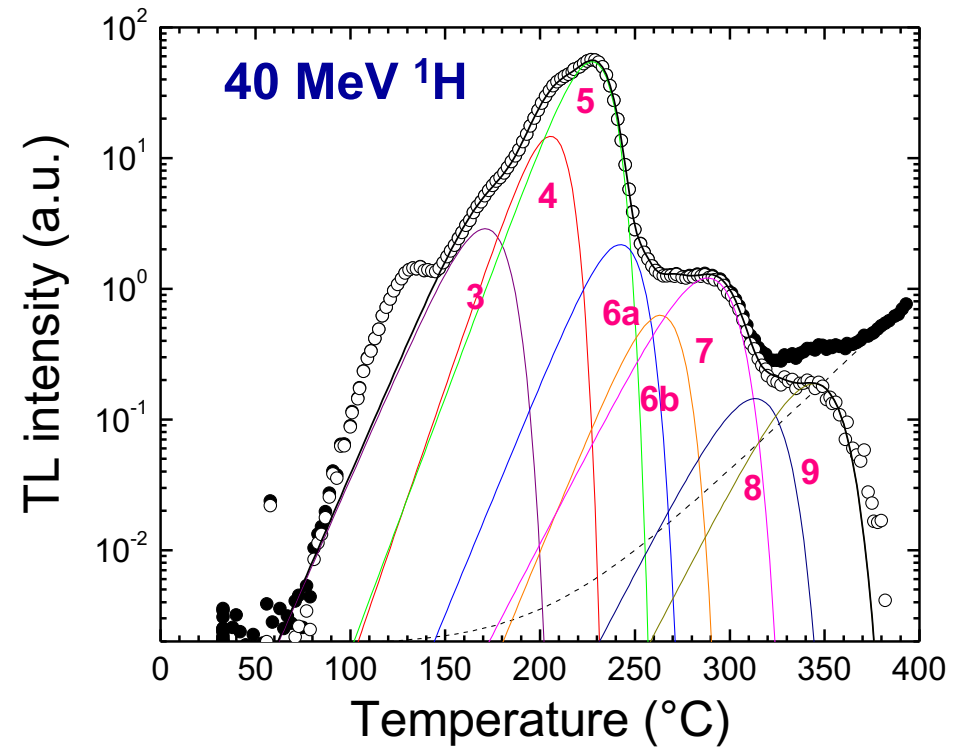
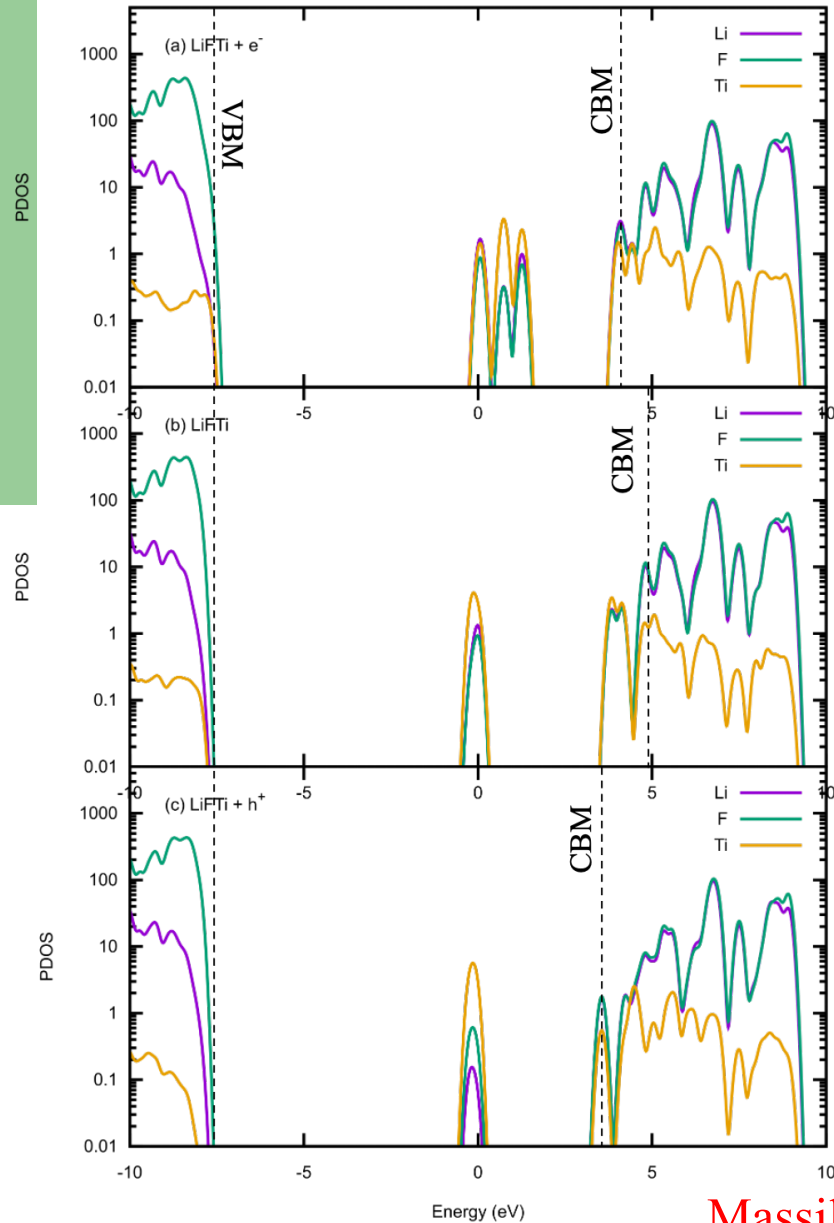
LiF:Ti with a hole after relaxation

Atom symbols

- ❖ Grey: F
- ❖ Green: Li
- ❖ Cyan: Ti



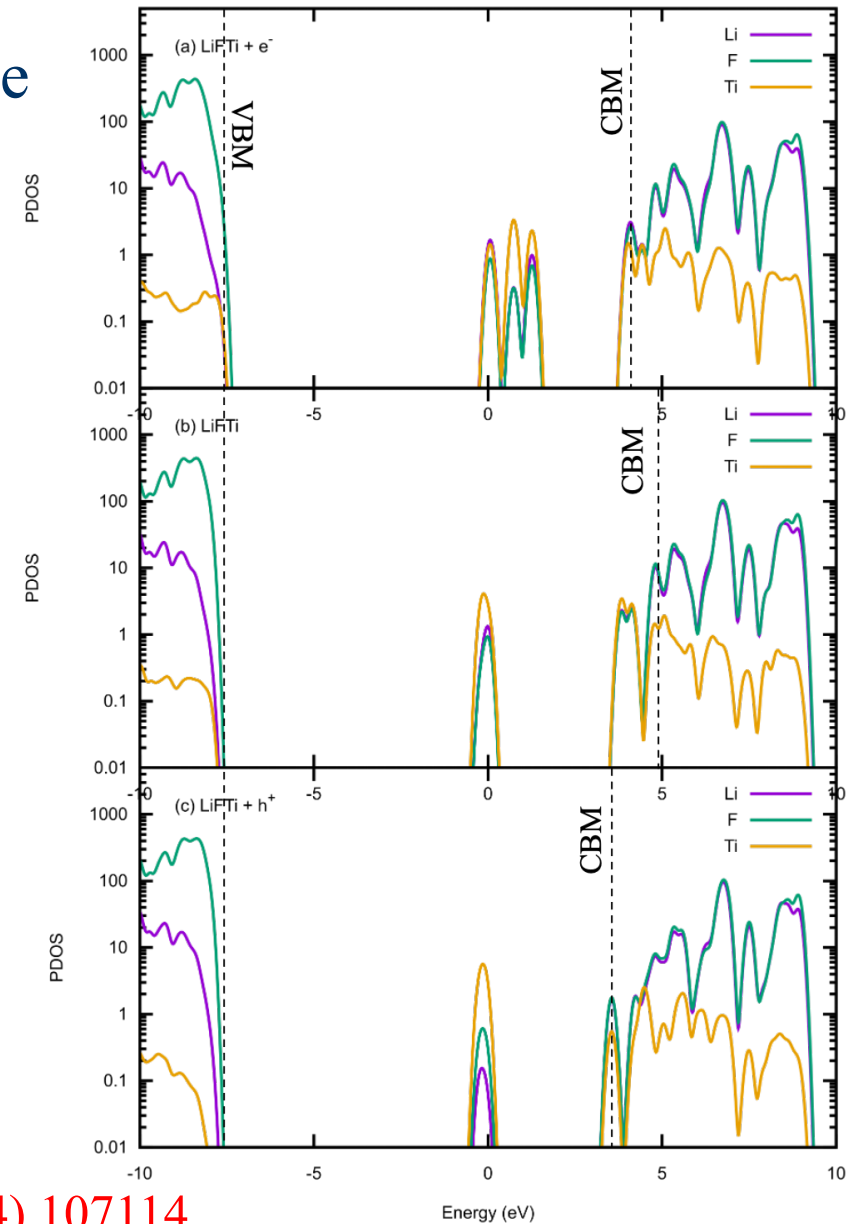
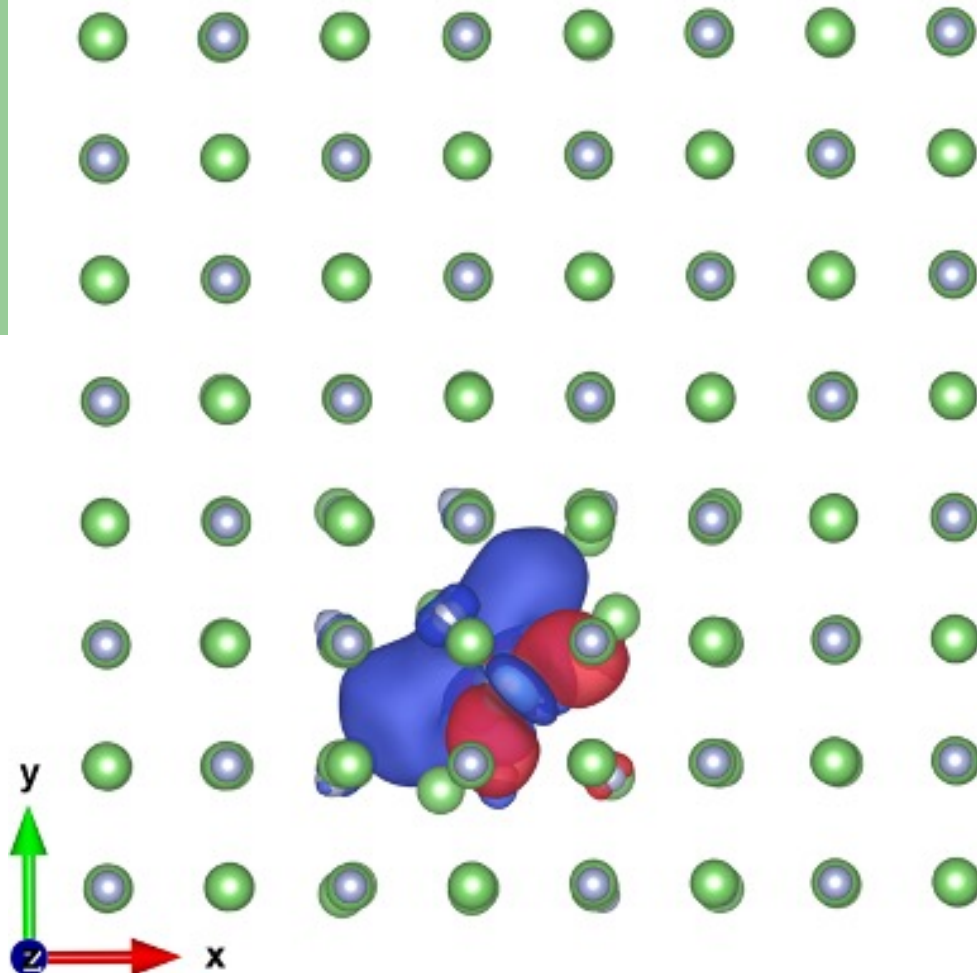
Density of states for LiF:Ti



G Massillon-JL, PhD Thesis UNAM 2006

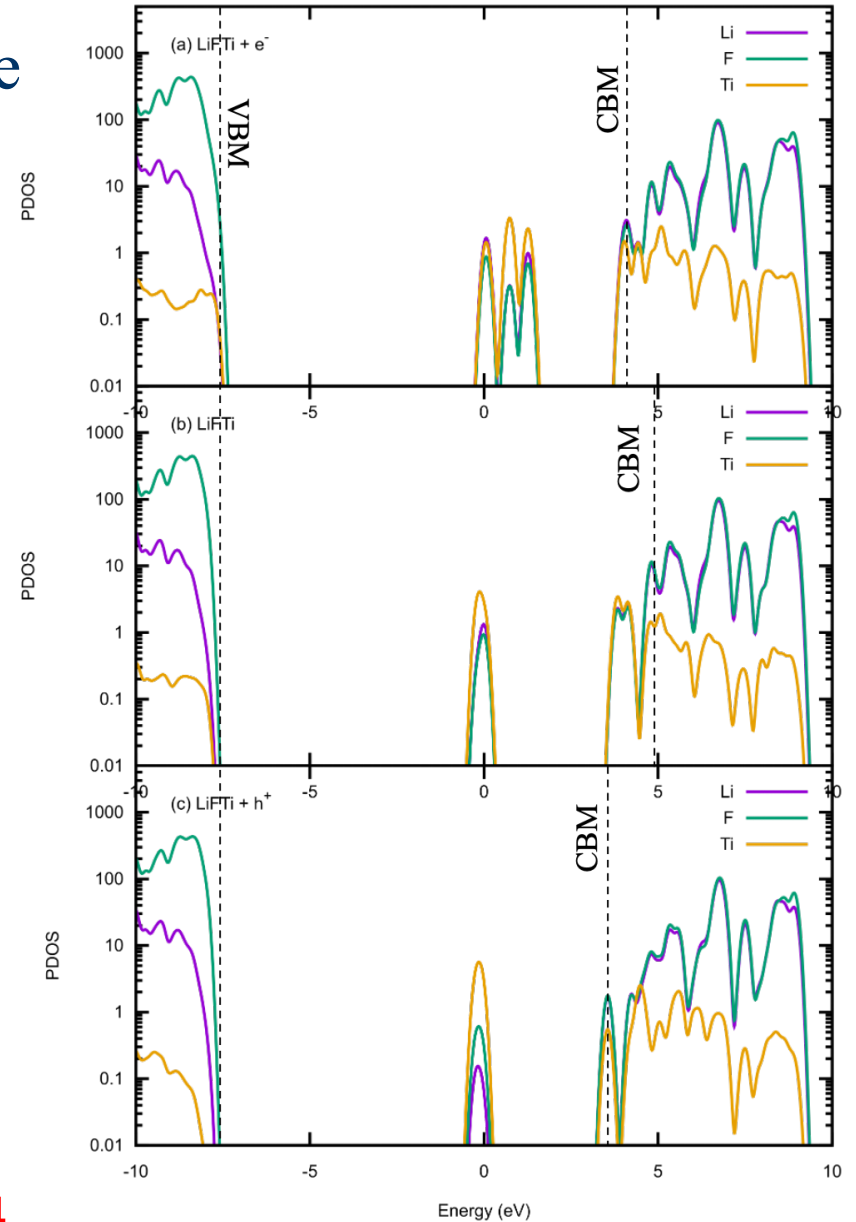
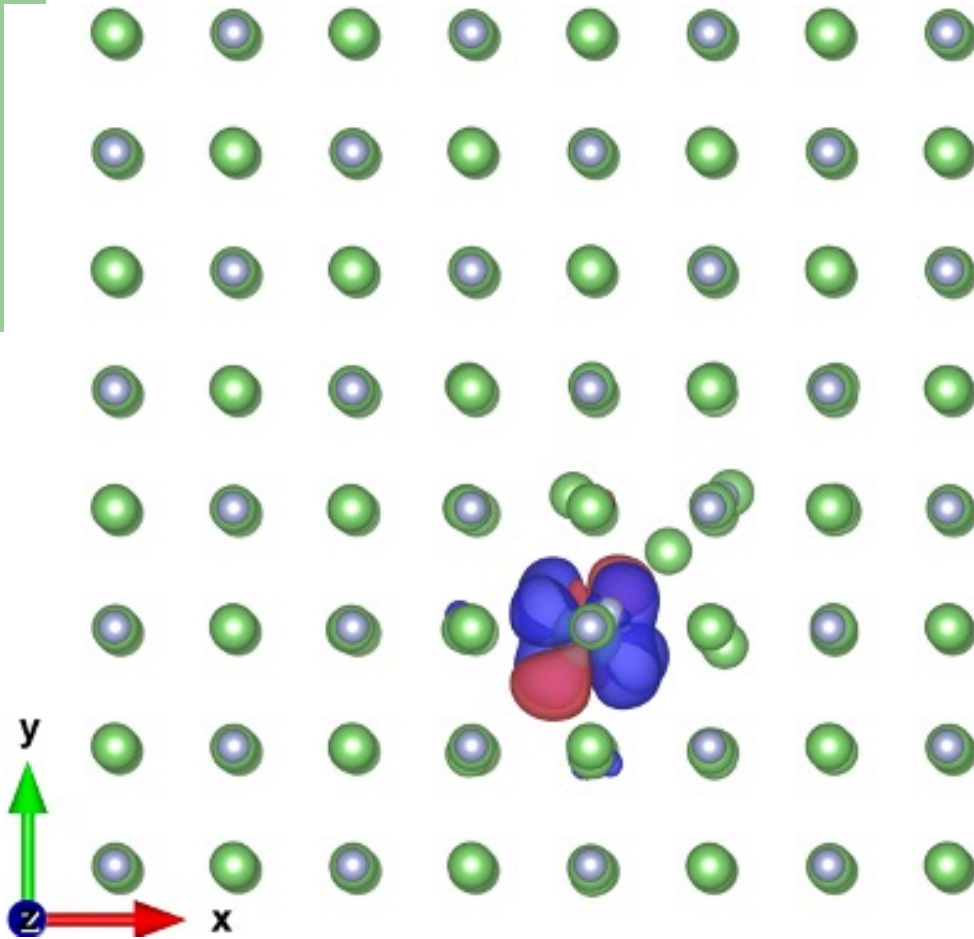
Defect states and electron localization in LiF:Ti

Spin density isosurface: Ti 4p-state



Defect states and hole localization in LiF:Ti

Spin density isosurface: Ti 3d-state



Defect formation energies

Defect formation energy and Thermodynamic transition level, $\varepsilon^{therm}(q_1/q_2)$

$$E_f(X^q) = E_{tot}(X^q) - E_{tot}(bulk) - \sum_i n_i \mu_i + qE_F$$

$$E_f(X^0; E_F = \varepsilon^{therm}(0/-1)) = E_f(X^{-1}; E_F = \varepsilon^{therm}(0/-1))$$

$$\varepsilon^{therm}(0/-1) = E_{tot}(X^{-1}) - E_{tot}(X^0) = [\varepsilon_{i+1}(N) + \varepsilon_{i+1}(N+1)]/2$$

$E_{tot}(X^q)$ and $E_{tot}(bulk)$ are the total energies of the system containing the defect, X , and of the perfect crystal, respectively

$\pm n_i$: number of atoms that have been added (+) or removed (-)

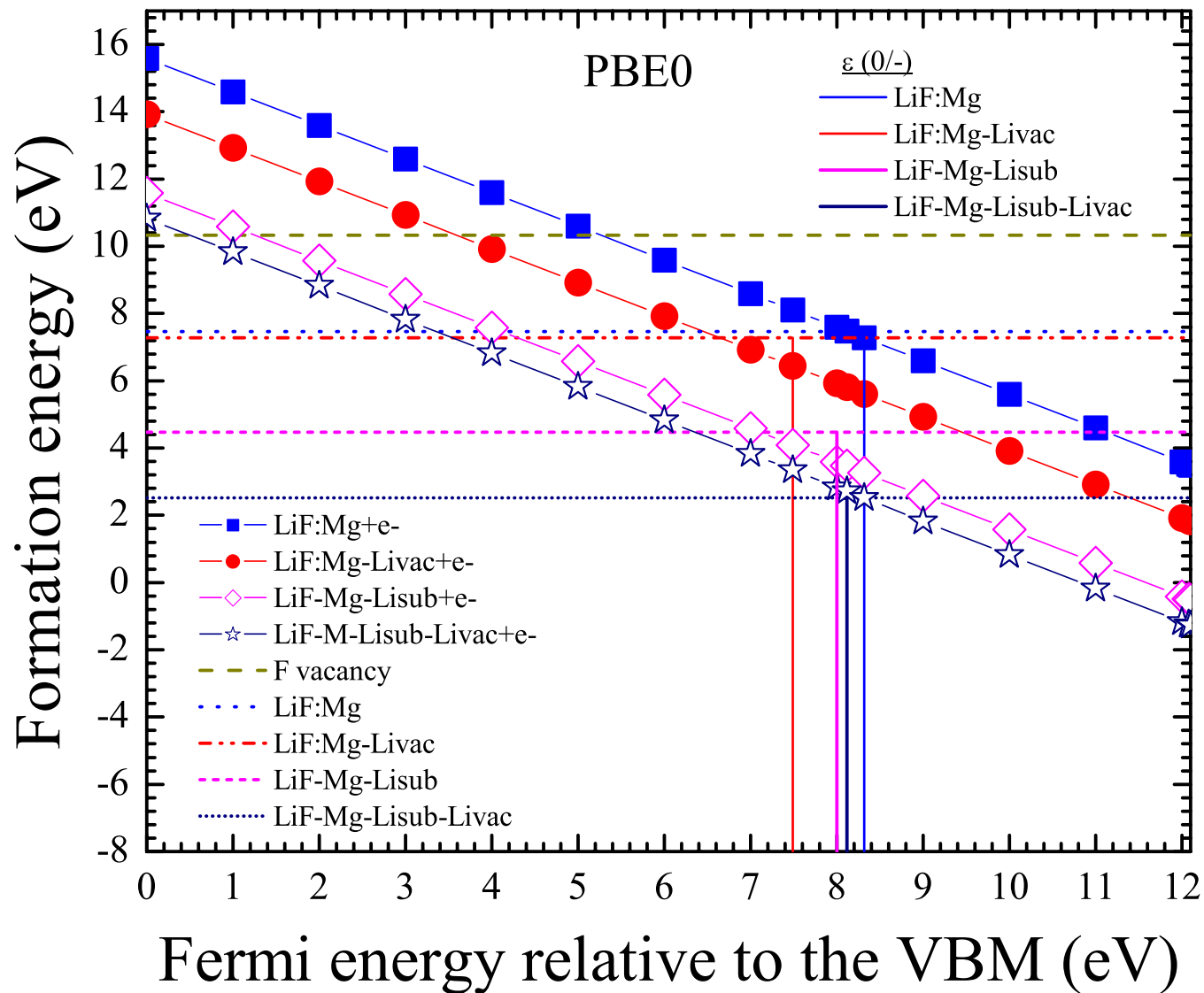
μ_i : chemical potentials

E_F : Fermi energy

E_f : Formation energy

$\varepsilon_{i+1}(N+1)$ eigenvalue of the highest occupied state of the $(N+1)$ -electron system

Defect formation energy



Defect formation energy

Table 2. Defect formation energies, E_f , and thermodynamic transition levels, $\varepsilon^{\text{therm}}$ (0/−1), of various defect-states in LiF at the PBE0 theory level. Energies in eV.

Defect-state	$E_f (E_F = 0)$	$\varepsilon^{\text{therm}}$ (0/ −1)
LiF		
LiF-F vacancy	10.33	
LiF:Mg	7.463	
LiF:Mg + e^-	15.34	8.32
LiF:Mg-Li _{vac}	7.29	
LiF:Mg-Li _{vac} + e^-	13.92	7.49
LiF-Mg-Li _{sub}	4.48	
LiF-Mg-Li _{sub} + e^-	11.58	8.00
LiF-Mg-Li _{sub} -Li _{vac}	2.53	
LiF-Mg-Li _{sub} -Li _{vac} + e^-	10.83	8.11

LiF:Mg, Summary

- The Mg interstitial creates a void for electron traps and is stable under normal conditions
- All charged defects are created by radiation and stables
- It is possible to identify the electron localization and quantify the energy loss for the defect's formation

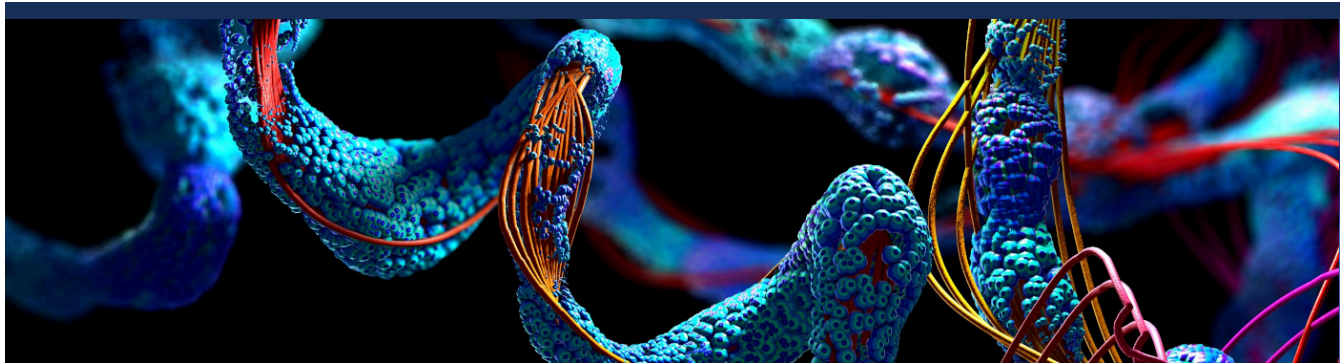
Not all the energy deposited into the dosimeter's sensitive volume is transformed to a certain response

LiF:Ti, Summary

- In the presence of excess electrons, Ti stays in an interstitial position.
- Excess electrons are localized in the Ti $4p$ -orbitals
- In the presence of holes, Ti becomes a substitutional Li atom and the Li is moved to a tetrahedral interstitial position.
- Holes are localized in the Ti $3d$ -orbitals which are recombination centers



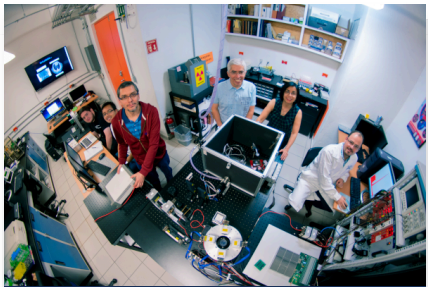
Ti dopant plays a dual character in LiF when exposed to ionizing radiation



Maestría en Ciencias Físicas

El egresado de esta maestría tendrá: Conocimiento sólido conceptual y operativo de la Física, en general, así como del campo de conocimiento seleccionado, en particular. Alta capacidad en el manejo de metodologías y técnicas teóricas o experimentales, particularmente [ver más...](#)

Más Información



Maestría en Física Médica

El egresado de esta maestría tendrá una formación básica y un dominio conceptual, y operativo de las aplicaciones de la Física en Medicina, que permitirá su futuro desempeño como Físico Médico Clínico en servicios de tratamiento y diagnóstico de enfermedades, o como profesional [ver más...](#)

Más Información



Doctorado en Ciencias Físicas

El egresado de este doctorado habrá adquirido un sólido dominio conceptual y operativo de la Física, así como un conocimiento profundo y actualizado de su línea de investigación. Asimismo, prepara al alumno para realizar labores de docencia y de divulgación de alto nivel académico. [ver más...](#)

Más Información

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Convocatoria

- POSDOC 2024
- POSDOC 2023
- POSDOC 2022
- POSDOC 2021

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Inicio / Formación académica / POSDOC

Programa de Becas Posdoctorales en la UNAM (POSDOC)



OBJETIVO:

Fortalecer el quehacer científico y docente de alto nivel, apoyando a recién doctorados y doctoradas para que desarrollen un proyecto de investigación novedoso en la UNAM.

DIRIGIDO A:

Recién doctorados y doctoradas de cualquier institución de reconocido prestigio, dentro de los cinco años previos a la fecha de inicio de la estancia posdoctoral; deberán tener una productividad demostrada por medio de obra publicada o aceptada para su publicación en revistas especializadas de prestigio internacional u otros medios de reconocida calidad académica y no deberán de tener contrato de trabajo con la UNAM al momento de iniciar la beca ni durante el periodo de la estancia.

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Un año, con posibilidad de una renovación por un año más, improrrogable.

Ingreso al GeDGAPA
Servicios en línea

Fechas destacadas
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Periodo 2024 - II

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